



# FDD86250

## N-Channel Shielded Gate PowerTrench<sup>®</sup> MOSFET

150 V, 51 A, 22 mΩ

### Features

- Shielded Gate MOSFET Technology
- Max  $r_{DS(on)}$  = 22 mΩ at  $V_{GS} = 10$  V,  $I_D = 8$  A
- Max  $r_{DS(on)}$  = 31 mΩ at  $V_{GS} = 6$  V,  $I_D = 6.5$  A
- 100% UIL tested
- RoHS Compliant

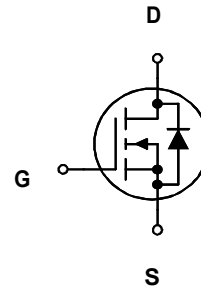
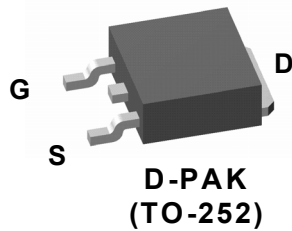


### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance.

### Application

- DC - DC Conversion



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	150	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous	$T_C = 25^\circ\text{C}$ (Note 5)	51
	-Continuous	$T_C = 100^\circ\text{C}$ (Note 5)	27
	-Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	8
	-Pulsed	(Note 4)	164
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3)	180
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	132
	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1a)	3.1
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.94	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	40	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD86250	FDD86250	D-PAK(TO-252)	13 "	16 mm	2500 units

## Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		106		$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.0	2.9	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		-10		$\text{mV}/^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$		18.4	22	m $\Omega$
		$V_{GS} = 6\text{ V}, I_D = 6.5\text{ A}$		21.4	31	
		$V_{GS} = 10\text{ V}, I_D = 8\text{ A}, T_J = 125\text{ }^\circ\text{C}$		35.8	45	
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 8\text{ A}$		28		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		1585	2110	pF
$C_{oss}$	Output Capacitance			167	225	pF
$C_{rss}$	Reverse Transfer Capacitance			7	15	pF
$R_g$	Gate Resistance			0.6		$\Omega$

### Switching Characteristics

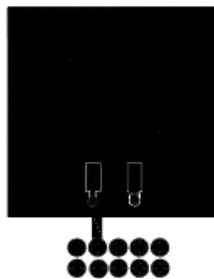
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\text{ V}, I_D = 8\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		11.2	20	ns	
$t_r$	Rise Time			3.7	10	ns	
$t_{d(off)}$	Turn-Off Delay Time			20	32	ns	
$t_f$	Fall Time			4	10	ns	
$Q_g$	Total Gate Charge		$V_{GS} = 0\text{ V to } 10\text{ V}$		23	33	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V to } 5\text{ V}$	$V_{DD} = 75\text{ V},$ $I_D = 8\text{ A}$		12.8	18	nC
$Q_{gs}$	Gate to Source Charge				6.7		nC
$Q_{gd}$	Gate to Drain "Miller" Charge				4.7		nC

### Drain-Source Diode Characteristics

$V_{SD}$	Source-Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 8\text{ A}$ (Note 2)		0.78	1.3	V
		$V_{GS} = 0\text{ V}, I_S = 2.6\text{ A}$ (Note 2)		0.73	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		71	113	ns
$Q_{rr}$	Reverse Recovery Charge			104	166	nC

#### Notes:

- 1:  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a)  $40\text{ }^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz. copper



b)  $96\text{ }^\circ\text{C/W}$  when mounted on a minimum pad

2: Pulse Test: Pulse Width <  $300\text{ }\mu\text{s}$ , Duty cycle < 2.0%.

3: Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 1.0\text{ mH}$ ,  $I_{AS} = 19\text{ A}$ ,  $V_{DD} = 135\text{ V}$ ,  $V_{GS} = 10\text{ V}$ .

4: Pulsed  $I_D$  please refer to Fig 11 SOA graph for more details.

5: Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.

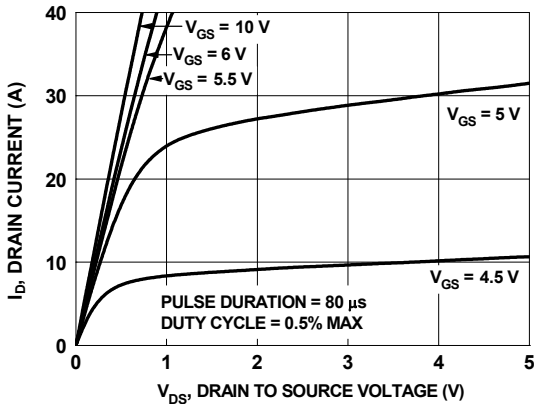


Figure 1. On-Region Characteristics

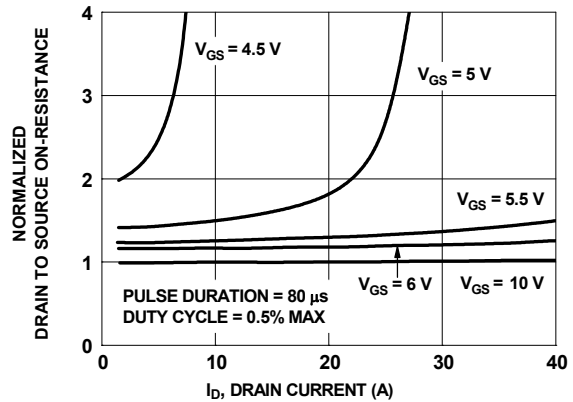


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

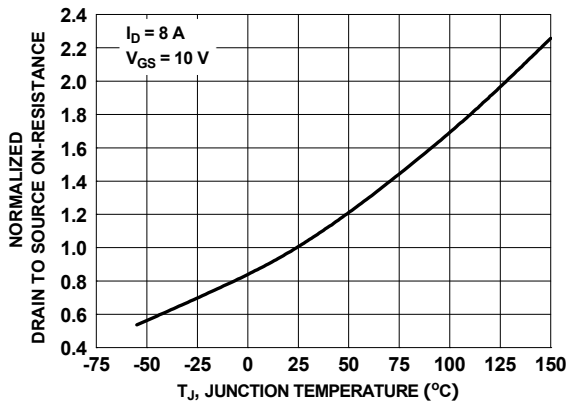


Figure 3. Normalized On-Resistance vs. Junction Temperature

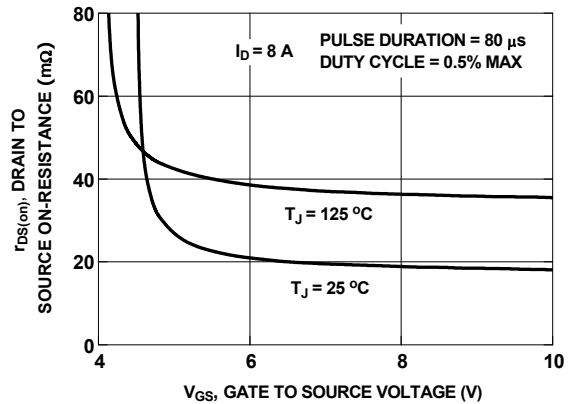


Figure 4. On-Resistance vs. Gate to Source Voltage

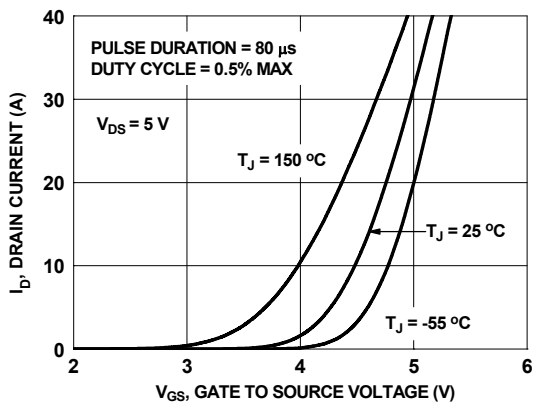


Figure 5. Transfer Characteristics

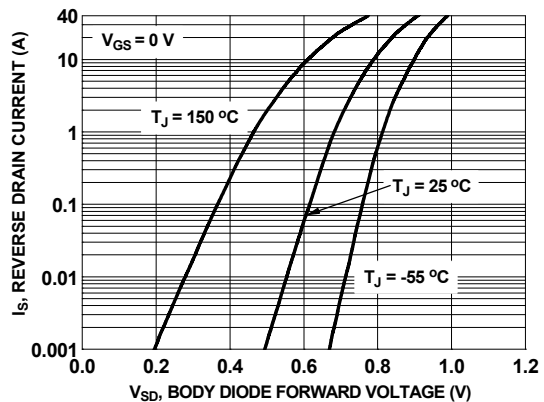
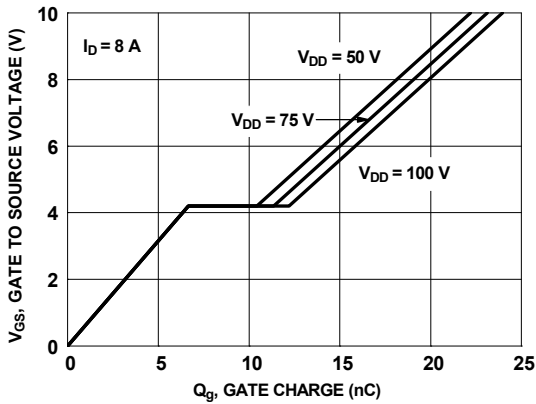
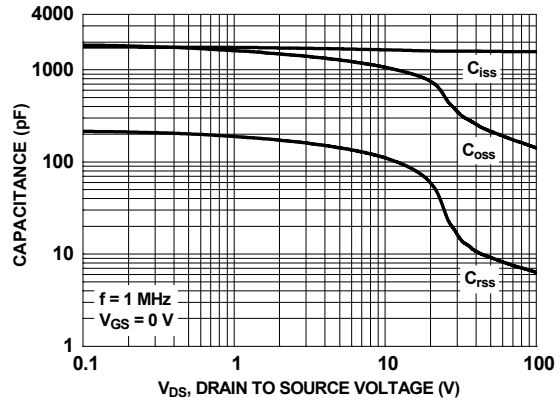


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

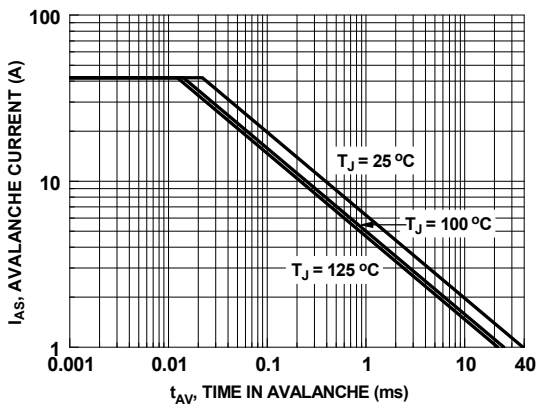
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted.



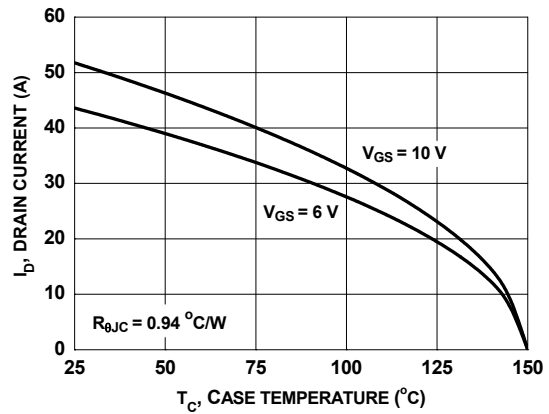
**Figure 7. Gate Charge Characteristics**



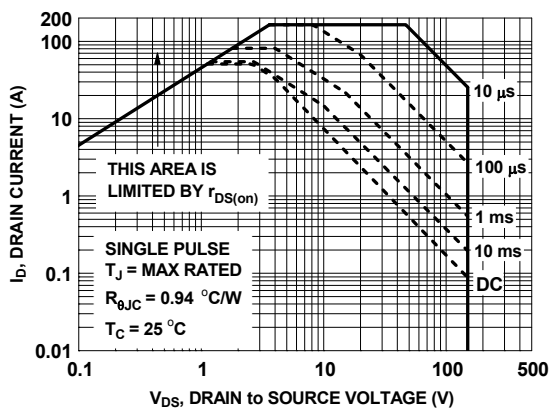
**Figure 8. Capacitance vs. Drain to Source Voltage**



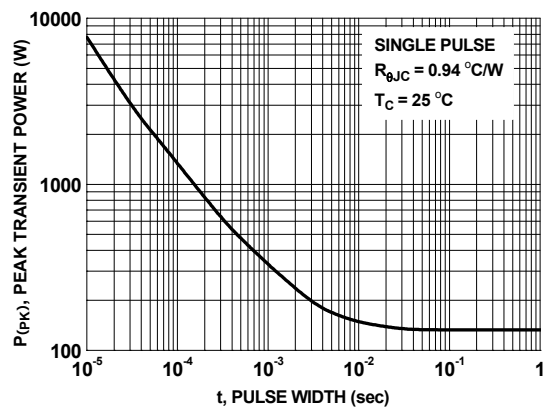
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**

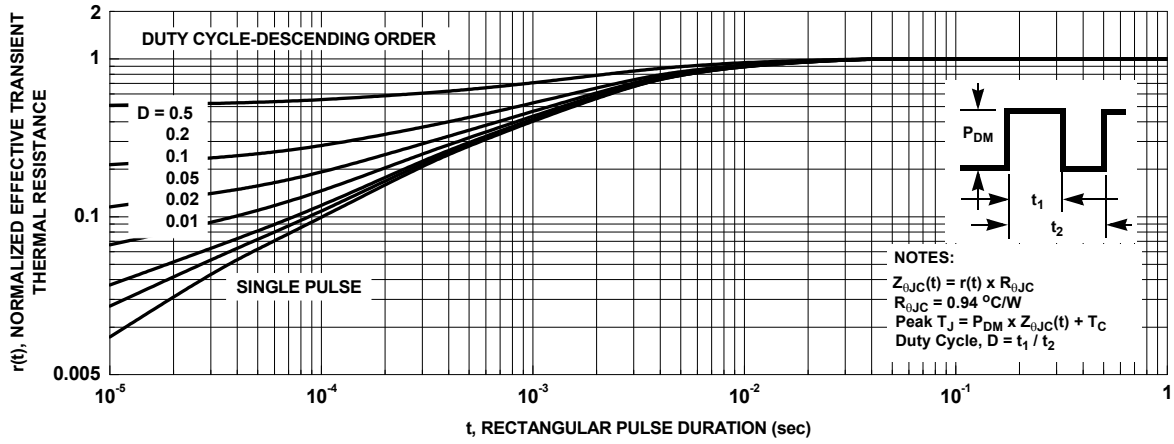


**Figure 11. Forward Bias Safe Operating Area**

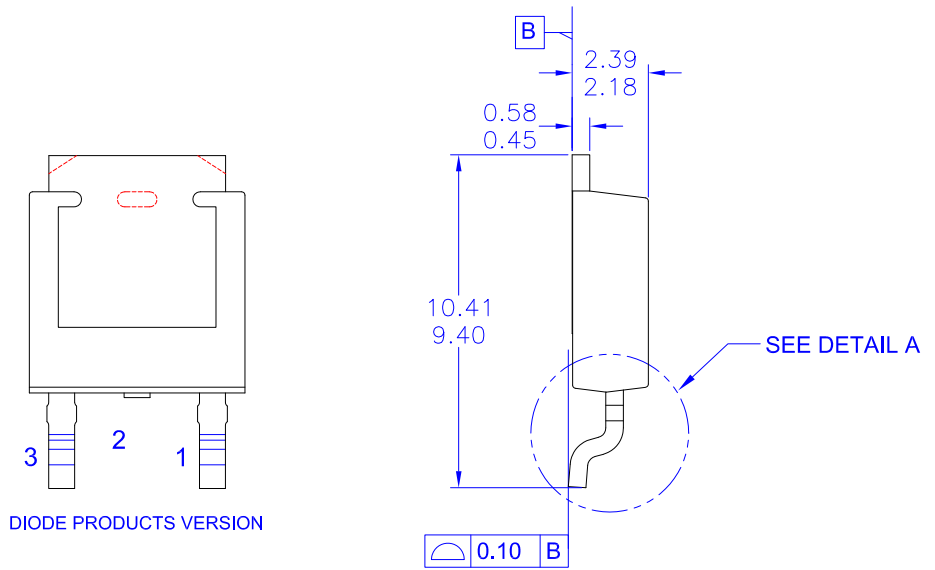
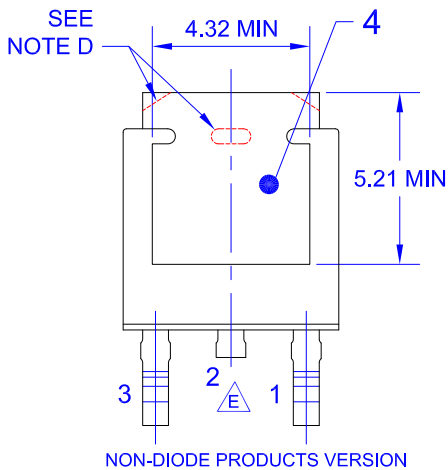
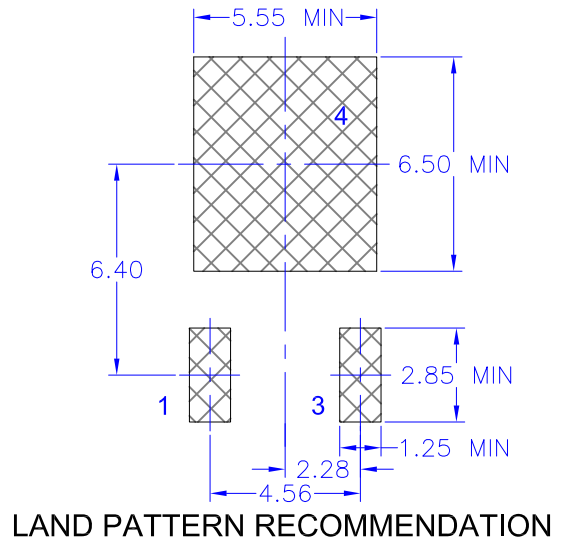
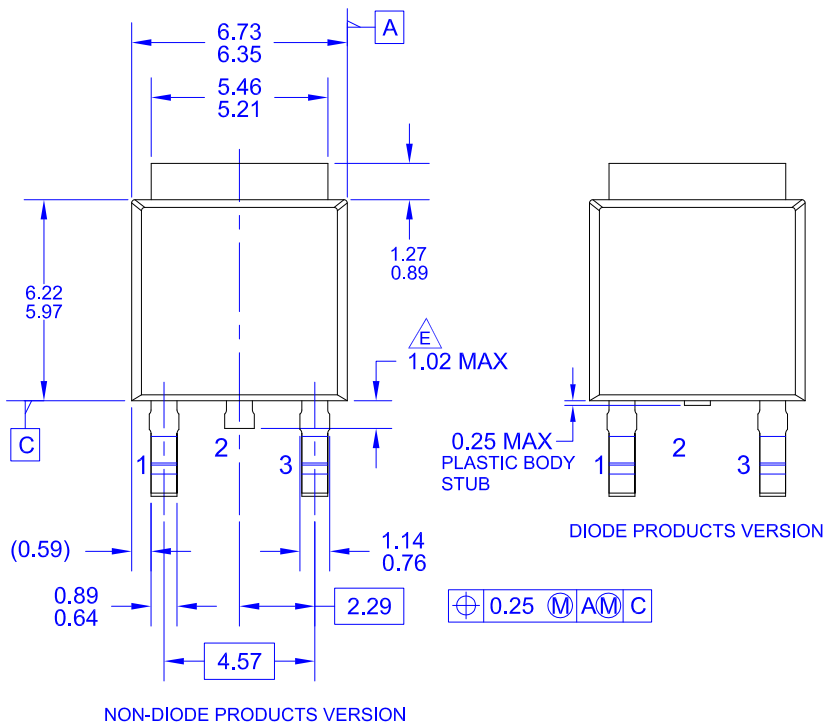


**Figure 12. Single Pulse Maximum Power Dissipation**

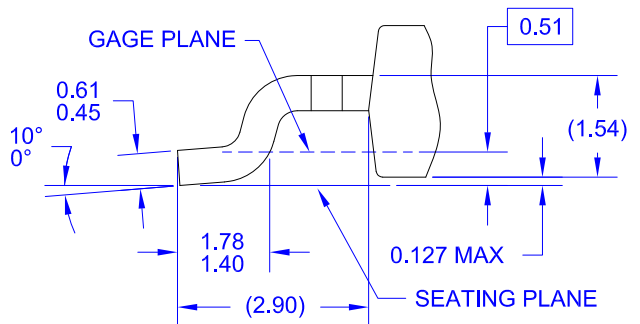
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.



**Figure 13. Junction-to-Case Transient Thermal Response Curve**



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
  - D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
  - E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
  - F) DIMENSIONS ARE EXCLUSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.
  - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
  - H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV10





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